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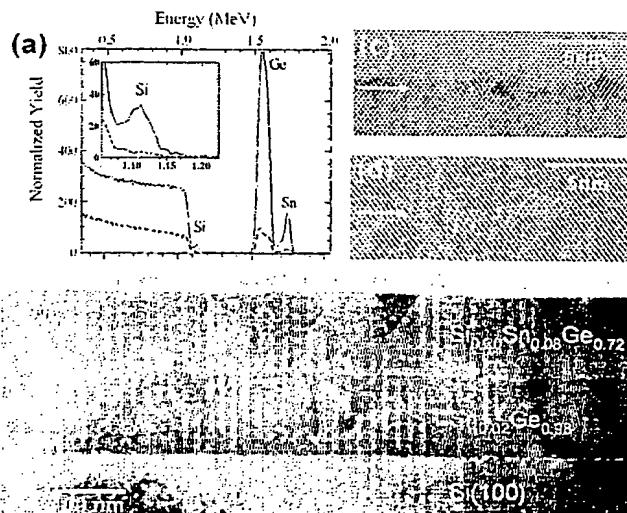
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[Continued on next page]

(54) Title: **Si_xSn_yGe_{1-x-y} AND RELATED ALLOY HETEROSTRUCTURES BASED ON Si, GE AND SN**



WO 2005/015609 A2

(57) **Abstract:** A novel method for synthesizing device-quality alloys and ordered phases in a Si-Ge-Sn system uses a UHV-CVD process and reactions of SnD₄ with SiH₃GeH₃. Using the method, single-phase Si_xSn_yGe_{1-x-y} semiconductors ($x \leq 0.25, y \leq 0.11$) are grown on Si via Ge_{1-x}Sn_x buffer layers. The Ge_{1-x}Sn_x buffer layers facilitate heteroepitaxial growth of the Si_xSn_yGe_{1-x-y} films and act as compliant templates that can conform structurally and absorb the differential strain imposed by the more rigid Si and Si-Ge-Sn materials. The SiH₃GeH₃ species was prepared using a new and high yield method that provided high purity semiconductor grade material.

**Declarations under Rule 4.17:**

- *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM). European patent (AT, BE,*
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